

WHAT IS CLAIMED IS:

1. A susceptor provided as a base of a substrate within a vacuum chamber in a thin film deposition apparatus, comprising:  
a susceptor main body, and  
a stepped portion provided on said susceptor main body to support  
5 said substrate from the bottom, having a size smaller than said substrate.

2. A surface processing method comprising the steps of:  
applying a blasting process on a surface of a susceptor that has SiO<sub>2</sub>  
as a main component, and  
etching the surface of said susceptor.

3. The surface processing method according to claim 2, further comprising the step of masking a portion of said susceptor forming contact with said substrate, prior to said step of blasting.

4. The surface processing method according to claim 2, further comprising the step of high pressure rinsing the surface of said susceptor, prior to said step of blasting.

5. The surface processing method according to claim 2, wherein said step of blasting is carried out using SiO<sub>2</sub> or SiC.

6. The surface processing method according to claim 2, further comprising the step of high pressure rinsing the surface of said susceptor after said etching.

7. A surface processing method of a glass jig that has SiO<sub>2</sub> as a main component, used in a neighborhood of a substrate and a wafer in a semiconductor formation process, a plasma display panel formation process, a plasma address liquid crystal formation process, and flat panel display  
5 formation process, comprising:

a first step of applying a blasting process on a surface of a subject to be processed,

a second step of etching the surface of said subject to be processed, and

10 a third step of cleaning said subject to be processed with one of means of:

(i) rinsing at high pressure,

(ii) rinsing with pure water and rinsing at high pressure.

8. A surface processing method of a thin film transistor substrate of a reflective type liquid crystal panel, comprising:

a first step of applying a blasting process on a surface of a TFT substrate,

5 a second step of etching the surface of said TFT substrate, and a third step of cleaning a subject to be processed with one of means of:

(i) rinsing at high pressure,

(ii) rinsing with pure water and rinsing at high pressure.

9. The surface processing method according to claim 7, further comprising the step of masking a portion of a susceptor forming contact with said substrate, prior to said step of blasting.

10. The surface processing method according to claim 7, further comprising the step of rinsing the surface of said susceptor at high pressure, prior to said step of blasting.

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